

IS61NLP6432A
IS61NLP6436A/IS61NVP6436A
IS61NLP12818A/IS61NVP12818A



64K x 32, 64K x 36, and 128K x 18
2Mb, PIPELINE 'NO WAIT' STATE BUS SRAM

PRELIMINARY INFORMATION
SEPTEMBER 2005

FEATURES

- 100 percent bus utilization
- No wait cycles between Read and Write
- Internal self-timed write cycle
- Individual Byte Write Control
- Single R/W (Read/Write) control pin
- Clock controlled, registered address, data and control
- Interleaved or linear burst sequence control using MODE input
- Three chip enables for simple depth expansion and address pipelining
- Power Down mode
- Common data inputs and data outputs
- CKE pin to enable clock and suspend operation
- JEDEC 100-pin TQFP package
- Power supply:
NVP: $V_{DD} 2.5V (\pm 5\%), V_{DDQ} 2.5V (\pm 5\%)$
NLP: $V_{DD} 3.3V (\pm 5\%), V_{DDQ} 3.3V/2.5V (\pm 5\%)$
- Industrial temperature available
- Lead-free available

DESCRIPTION

The 2 Meg 'NLP/NVP' product family feature high-speed, low-power synchronous static RAMs designed to provide a burstable, high-performance, 'no wait' state, device for networking and communications applications. They are organized as 64K words by 32 bits, 64K words by 36 bits, and 128K words by 18 bits, fabricated with ISSI's advanced CMOS technology.

Incorporating a 'no wait' state feature, wait cycles are eliminated when the bus switches from read to write, or write to read. This device integrates a 2-bit burst counter, high-speed SRAM core, and high-drive capability outputs into a single monolithic circuit.

All synchronous inputs pass through registers are controlled by a positive-edge-triggered single clock input. Operations may be suspended and all synchronous inputs ignored when Clock Enable, CKE is HIGH. In this state the internal device will hold their previous values.

All Read, Write and Deselect cycles are initiated by the ADV input. When the ADV is HIGH the internal burst counter is incremented. New external addresses can be loaded when ADV is LOW.

Write cycles are internally self-timed and are initiated by the rising edge of the clock inputs and when WE is LOW. Separate byte enables allow individual bytes to be written.

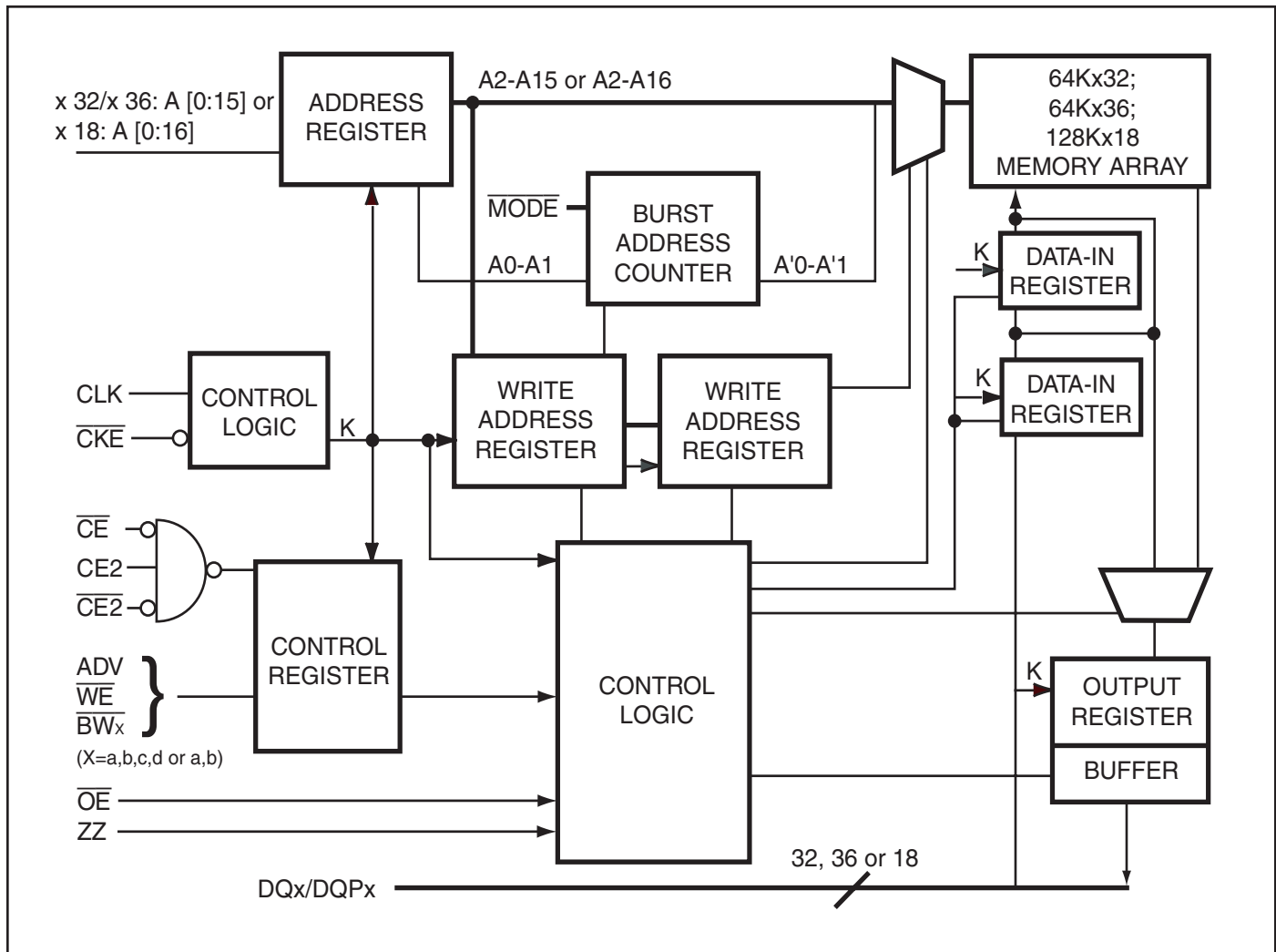
A burst mode pin (MODE) defines the order of the burst sequence. When tied HIGH, the interleaved burst sequence is selected. When tied LOW, the linear burst sequence is selected.

FAST ACCESS TIME

Symbol	Parameter	-250	-200	Units
t _{KQ}	Clock Access Time	2.6	3.1	ns
t _{KC}	Cycle Time	4	5	ns
	Frequency	250	200	MHz

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BLOCK DIAGRAM

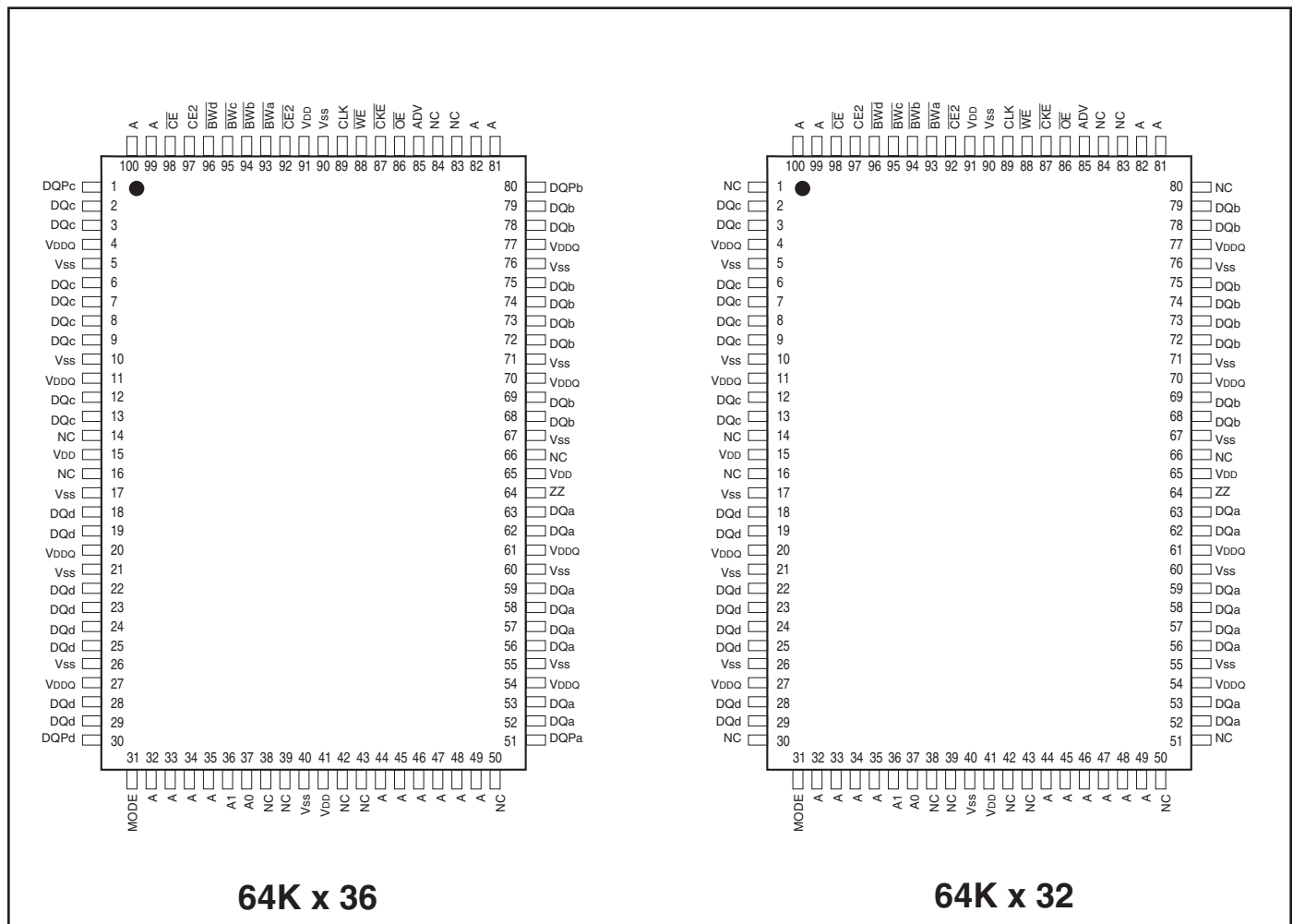


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PIN CONFIGURATION

100-Pin TQFP



PIN DESCRIPTIONS

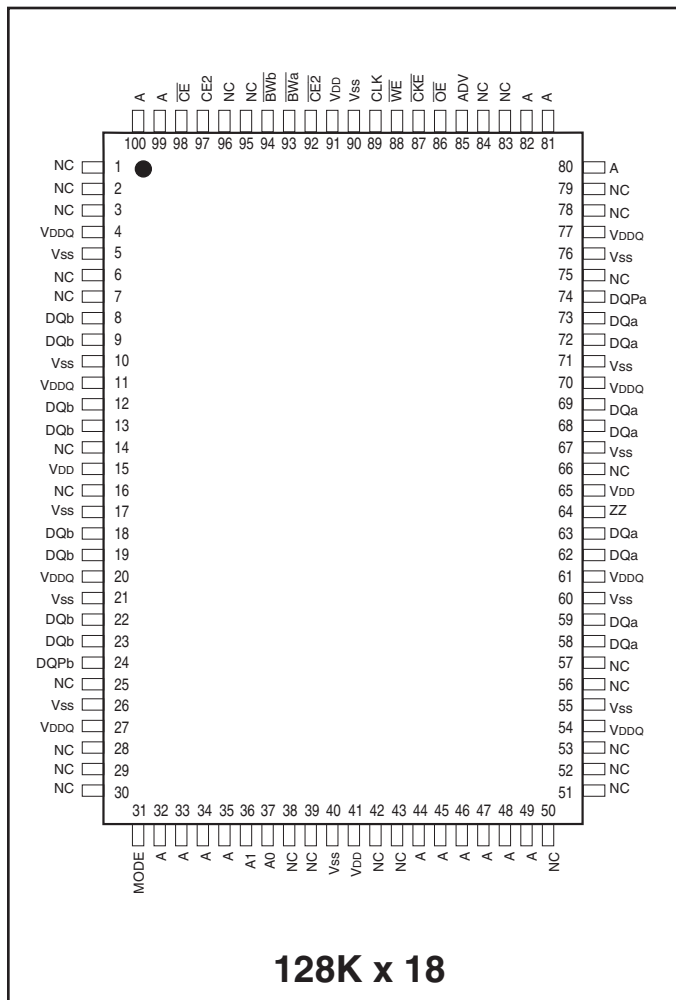
A0, A1	Synchronous Address Inputs. These pins must be tied to the two LSBs of the address bus.
A	Synchronous Address Inputs
CLK	Synchronous Clock
ADV	Synchronous Burst Address Advance
BW _a -BW _d	Synchronous Byte Write Enable
WE	Write Enable
CKE	Clock Enable
V _{ss}	Ground for Core
NC	Not Connected

\overline{CE} , $\overline{CE2}$, $\overline{CE2}$	Synchronous Chip Enable
OE	Output Enable
DQ _a -DQ _d	Synchronous Data Input/Output
DQP _a -DQP _d	Parity Data I/O
MODE	Burst Sequence Selection
V _{DD}	+3.3V/2.5V Power Supply
V _{SS}	Ground for output Buffer
V _{DDQ}	Isolated Output Buffer Supply: +3.3V/2.5V
ZZ	Snooze Enable

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PIN CONFIGURATION 100-Pin TQFP

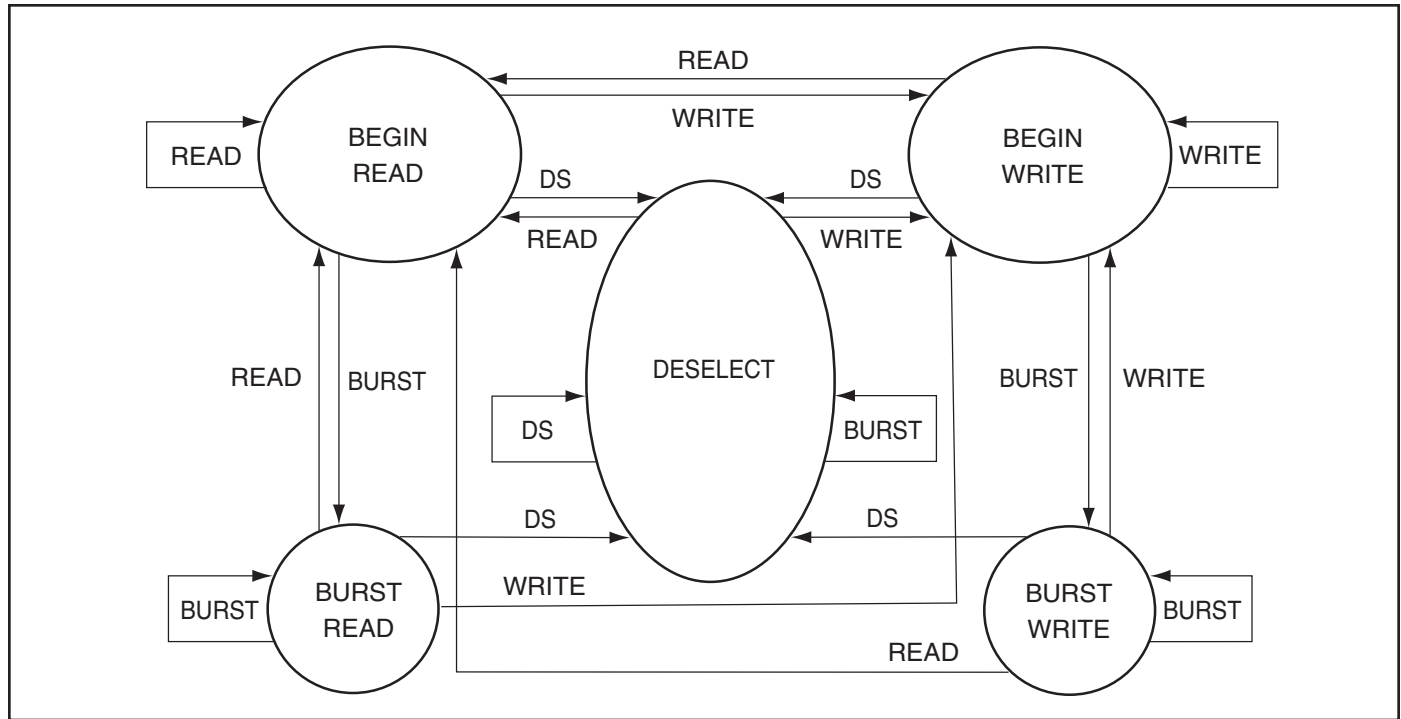


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DQP _a -DQP _d	Parity Data I/O
MODE	Burst Sequence Selection
V _{DD}	+3.3V/2.5V Power Supply
V _{SS}	Ground for output Buffer
V _{DDQ}	Isolated Output Buffer Supply: +3.3V/2.5V
ZZ	Snooze Enable

STATE DIAGRAM



SYNCHRONOUS TRUTH TABLE⁽¹⁾

Operation	Address Used	\overline{CE}	CE2	$\overline{CE2}$	ADV	\overline{WE}	$\overline{BW_x}$	\overline{OE}	\overline{CKE}	CLK
Not Selected	N/A	H	X	X	L	X	X	X	L	↑
Not Selected	N/A	X	L	X	L	X	X	X	L	↑
Not Selected	N/A	X	X	H	L	X	X	X	L	↑
Not Selected Continue	N/A	X	X	X	H	X	X	X	L	↑
Begin Burst Read	External Address	L	H	L	L	H	X	L	L	↑
Continue Burst Read	Next Address	X	X	X	H	X	X	L	L	↑
NOP/Dummy Read	External Address	L	H	L	L	H	X	H	L	↑
Dummy Read	Next Address	X	X	X	H	X	X	H	L	↑
Begin Burst Write	External Address	L	H	L	L	L	L	X	L	↑
Continue Burst Write	Next Address	X	X	X	H	X	L	X	L	↑
NOP/Write Abort	N/A	L	H	L	L	L	H	X	L	↑
Write Abort	Next Address	X	X	X	H	X	H	X	L	↑
Ignore Clock	Current Address	X	X	X	X	X	X	X	H	↑

Notes:

- "X" means don't care.
- The rising edge of clock is symbolized by ↑
- A continue deselect cycle can only be entered if a deselect cycle is executed first.
- $\overline{WE} = L$ means Write operation in Write Truth Table.
 $\overline{WE} = H$ means Read operation in Write Truth Table.
- Operation finally depends on status of asynchronous pins (ZZ and \overline{OE}).

ASYNCHRONOUS TRUTH TABLE⁽¹⁾

Operation	ZZ	\overline{OE}	I/O STATUS
Sleep Mode	H	X	High-Z
Read	L	L	DQ
	L	H	High-Z
Write	L	X	Din, High-Z
Deselected	L	X	High-Z

Notes:

1. X means "Don't Care".
2. For write cycles following read cycles, the output buffers must be disabled with \overline{OE} , otherwise data bus contention will occur.
3. Sleep Mode means power Sleep Mode where stand-by current does not depend on cycle time.
4. Deselected means power Sleep Mode where stand-by current depends on cycle time.

WRITE TRUTH TABLE (x18)

Operation	\overline{WE}	$\overline{Bw}a$	$\overline{Bw}b$
READ	H	X	X
WRITE BYTE a	L	L	H
WRITE BYTE b	L	H	L
WRITE ALL BYTES	L	L	L
WRITE ABORT/NOP	L	H	H

Notes:

1. X means "Don't Care".
2. All inputs in this table must meet setup and hold time around the rising edge of CLK.

WRITE TRUTH TABLE (x32/x36)

Operation	\overline{WE}	\overline{BWa}	\overline{BWb}	\overline{BWc}	\overline{BWd}
READ	H	X	X	X	X
WRITE BYTE a	L	L	H	H	H
WRITE BYTE b	L	H	L	H	H
WRITE BYTE c	L	H	H	L	H
WRITE BYTE d	L	H	H	H	L
WRITE ALL BYTES	L	L	L	L	L
WRITE ABORT/NOP	L	H	H	H	H

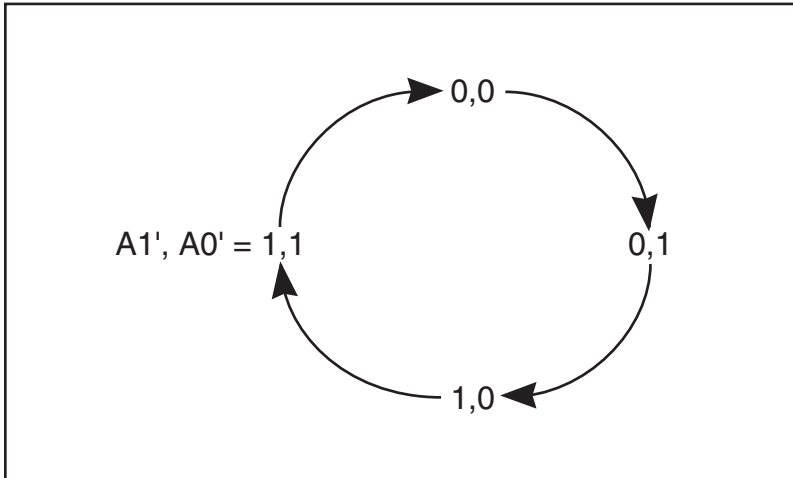
Notes:

1. X means "Don't Care".
2. All inputs in this table must be setup and hold time around the rising edge of CLK.

INTERLEAVED BURST ADDRESS TABLE (MODE = V_{DD} or NC)

External Address A1 A0	1st Burst Address A1 A0	2nd Burst Address A1 A0	3rd Burst Address A1 A0
00	01	10	11
01	00	11	10
10	11	00	01
11	10	01	00

LINEAR BURST ADDRESS TABLE (MODE = V_{SS})



ABSOLUTE MAXIMUM RATINGS⁽¹⁾

Symbol	Parameter	Value	Unit
T _{STG}	Storage Temperature	-65 to +150	°C
P _D	Power Dissipation	1.6	W
I _{OUT}	Output Current (per I/O)	100	mA
V _{IN} , V _{OUT}	Voltage Relative to V _{SS} for I/O Pins	-0.5 to V _{DDQ} + 0.3	V
V _{IN}	Voltage Relative to V _{SS} for for Address and Control Inputs	-0.3 to 4.6	V

Notes:

1. Stress greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.
2. This device contains circuitry to protect the inputs against damage due to high static voltages or electric fields; however, precautions may be taken to avoid application of any voltage higher than maximum rated voltages to this high-impedance circuit.
3. This device contains circuitry that will ensure the output devices are in High-Z at power up.

OPERATING RANGE (IS61NLPx)

Range	Ambient Temperature	V _{DD}	V _{DDQ}
Commercial	0°C to +70°C	3.3V ± 5%	3.3V / 2.5V ± 5%
Industrial	-40°C to +85°C	3.3V ± 5%	3.3V / 2.5V ± 5%

OPERATING RANGE (IS61NVPx)

Range	Ambient Temperature	V _{DD}	V _{DDQ}
Commercial	0°C to +70°C	2.5V ± 5%	2.5V ± 5%
Industrial	-40°C to +85°C	2.5V ± 5%	2.5V ± 5%

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DC ELECTRICAL CHARACTERISTICS (Over Operating Range)

Symbol	Parameter	Test Conditions	3.3V		2.5V		Unit
			Min.	Max.	Min.	Max.	
V _{OH}	Output HIGH Voltage	I _{OH} = -4.0 mA (3.3V) I _{OH} = -1.0 mA (2.5V)	2.4	—	2.0	—	V
V _{OL}	Output LOW Voltage	I _{OL} = 8.0 mA (3.3V) I _{OL} = 1.0 mA (2.5V)	—	0.4	—	0.4	V
V _{IH}	Input HIGH Voltage		2.0	V _{DD} + 0.3	1.7	V _{DD} + 0.3	V
V _{IL}	Input LOW Voltage		-0.3	0.8	-0.3	0.7	V
I _{LI}	Input Leakage Current	V _{SS} ≤ V _{IN} ≤ V _{DD} ⁽¹⁾	-5	5	-5	5	μA
I _{LO}	Output Leakage Current	V _{SS} ≤ V _{OUT} ≤ V _{DDQ} , \overline{OE} = V _{IH}	-5	5	-5	5	μA

POWER SUPPLY CHARACTERISTICS⁽¹⁾ (Over Operating Range)

Symbol	Parameter	Test Conditions	Temp. range	-250 MAX		-200 MAX		Unit
				x18	x32/x36	x18	x32/x36	
I _{CC}	AC Operating Supply Current	Device Selected, \overline{OE} = V _{IH} , ZZ ≤ V _{IL} , All Inputs ≤ 0.2V or ≥ V _{DD} - 0.2V, Cycle Time ≥ t _{kc} min.	Com. Ind.	225 250	225 250	200 210	200 210	mA
I _{SB}	Standby Current TTL Input	Device Deselected, V _{DD} = Max., All Inputs ≤ V _{IL} or ≥ V _{IH} , ZZ ≤ V _{IL} , f = Max.	Com. Ind.	90 100	90 100	90 100	90 100	mA
I _{SB1}	Standby Current CMOS Input	Device Deselected, V _{DD} = Max., V _{IN} ≤ V _{SS} + 0.2V or ≥ V _{DD} - 0.2V f = 0	Com. Ind. typ. ⁽²⁾	70 75 40	70 75	70 75 40	70 75	mA
I _{SB2}	Sleep Mode	ZZ > V _{IH}	Com. Ind. typ. ⁽²⁾	30 35 20	30 35	30 35 20	30 35	mA

Note:

- MODE pin has an internal pullup and should be tied to V_{DD} or V_{SS}. It exhibits ±100μA maximum leakage current when tied to ≤ V_{SS} + 0.2V or ≥ V_{DD} - 0.2V.
- Typical values are measured at V_{DD} = 3.3V, T_A = 25°C and not 100% tested.

CAPACITANCE^(1,2)

Symbol	Parameter	Conditions	Max.	Unit
C _{IN}	Input Capacitance	V _{IN} = 0V	6	pF
C _{OUT}	Input/Output Capacitance	V _{OUT} = 0V	8	pF

Notes:

1. Tested initially and after any design or process changes that may affect these parameters.
2. Test conditions: T_A = 25°C, f = 1 MHz, V_{DD} = 3.3V.

3.3V I/O AC TEST CONDITIONS

Parameter	Unit
Input Pulse Level	0V to 3.0V
Input Rise and Fall Times	1.5 ns
Input and Output Timing and Reference Level	1.5V
Output Load	See Figures 1 and 2

3.3V I/O OUTPUT LOAD EQUIVALENT

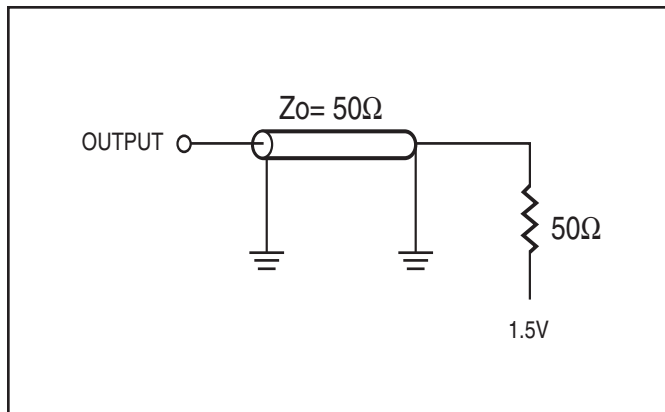


Figure 1

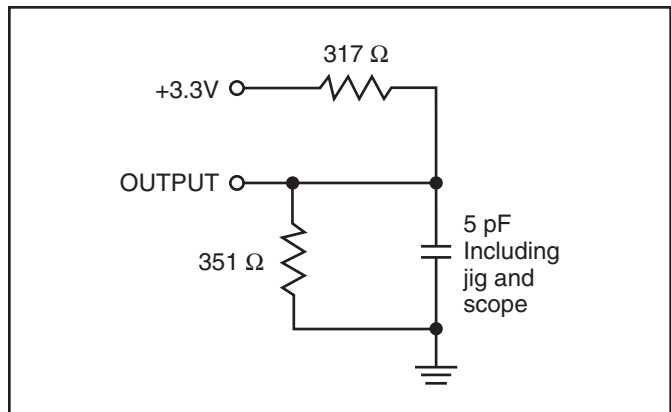


Figure 2

2.5V I/O AC TEST CONDITIONS

Parameter	Unit
Input Pulse Level	0V to 2.5V
Input Rise and Fall Times	1.5 ns
Input and Output Timing and Reference Level	1.25V
Output Load	See Figures 3 and 4

2.5V I/O OUTPUT LOAD EQUIVALENT

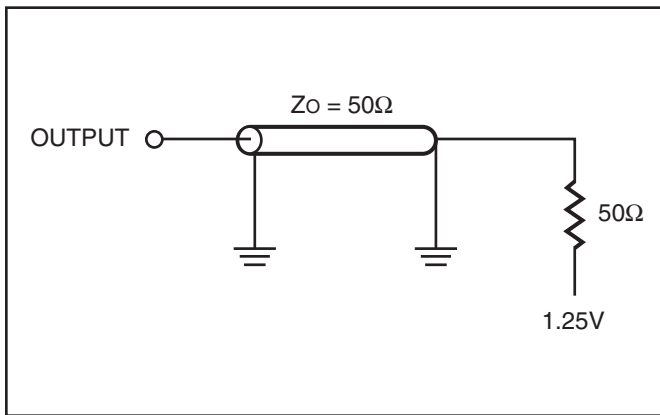


Figure 3

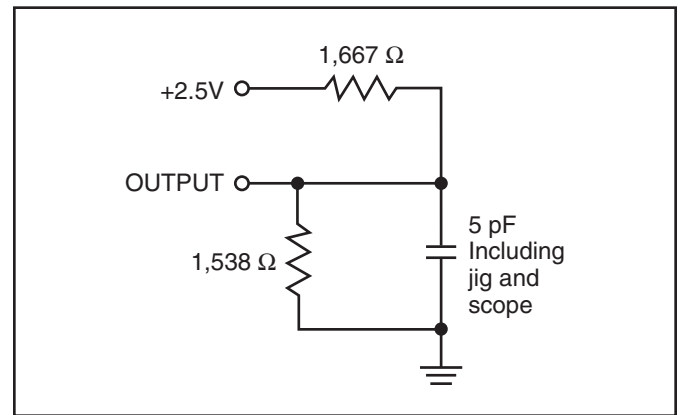


Figure 4



READ/WRITE CYCLE SWITCHING CHARACTERISTICS⁽¹⁾ (Over Operating Range)

Symbol	Parameter	-250		-200		Unit
		Min.	Max.	Min.	Max.	
fmax	Clock Frequency	—	250	—	200	MHz
t _{KC}	Cycle Time	4.0	—	5	—	ns
t _{KH}	Clock High Time	1.7	—	2	—	ns
t _{KL}	Clock Low Time	1.7	—	2	—	ns
t _{KQ}	Clock Access Time	—	2.6	—	3.1	ns
t _{KQX} ⁽²⁾	Clock High to Output Invalid	0.8	—	1.5	—	ns
t _{KQLZ} ^(2,3)	Clock High to Output Low-Z	0.8	—	1	—	ns
t _{KQHZ} ^(2,3)	Clock High to Output High-Z	—	2.6	—	3.0	ns
t _{OEQ}	Output Enable to Output Valid	—	2.8	—	3.1	ns
t _{OELZ} ^(2,3)	Output Enable to Output Low-Z	0	—	0	—	ns
t _{OEHZ} ^(2,3)	Output Disable to Output High-Z	—	2.6	—	3.0	ns
t _{AS}	Address Setup Time	1.2	—	1.4	—	ns
t _{WS}	Read/Write Setup Time	1.2	—	1.4	—	ns
t _{CES}	Chip Enable Setup Time	1.2	—	1.4	—	ns
t _{SE}	Clock Enable Setup Time	1.2	—	1.4	—	ns
t _{ADVS}	Address Advance Setup Time	1.2	—	1.4	—	ns
t _{DS}	Data Setup Time	1.2	—	1.4	—	ns
t _{AH}	Address Hold Time	0.3	—	0.4	—	ns
t _{HE}	Clock Enable Hold Time	0.3	—	0.4	—	ns
t _{WH}	Write Hold Time	0.3	—	0.4	—	ns
t _{CEH}	Chip Enable Hold Time	0.3	—	0.4	—	ns
t _{ADVH}	Address Advance Hold Time	0.3	—	0.4	—	ns
t _{DH}	Data Hold Time	0.3	—	0.4	—	ns
t _{PDS}	ZZ High to Power Down	—	2	—	2	cyc
t _{PUS}	ZZ Low to Power Down	—	2	—	2	cyc

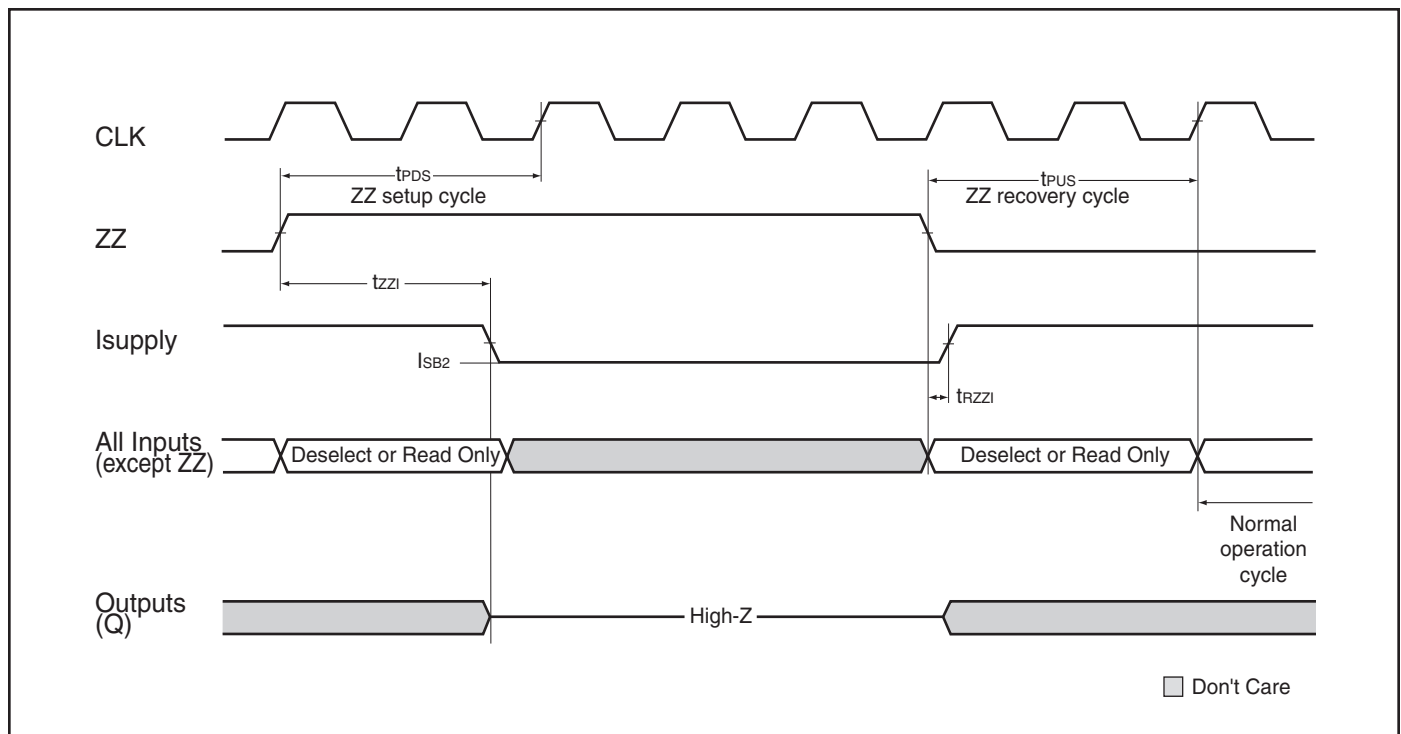
Notes:

1. Configuration signal MODE is static and must not change during normal operation.
2. Guaranteed but not 100% tested. This parameter is periodically sampled.
3. Tested with load in Figure 2.

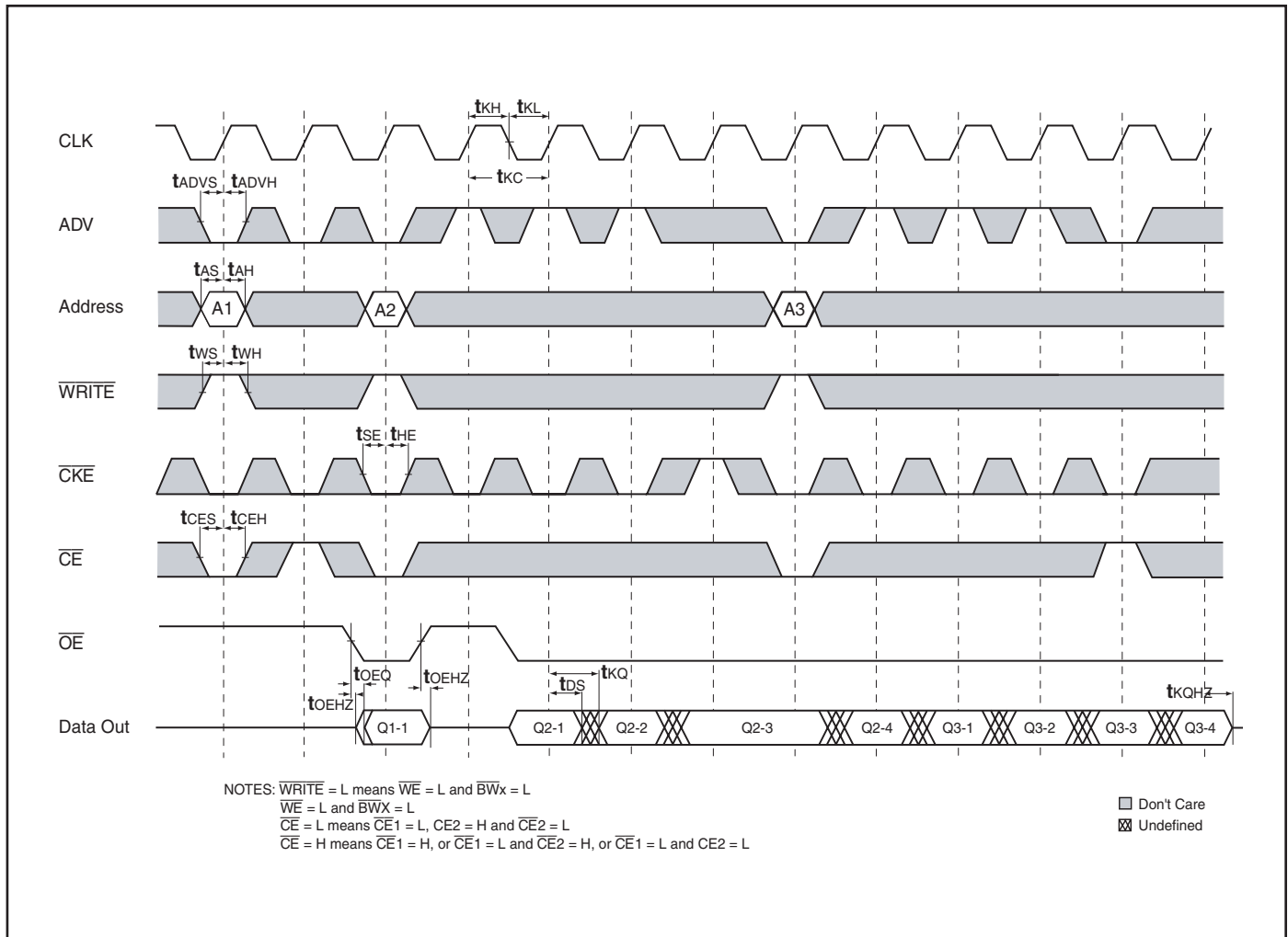
SLEEP MODE ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Conditions	Min.	Max.	Unit
I_{SB2}	Current during SLEEP MODE	$ZZ \geq V_{IH}$		35	mA
t_{PDS}	ZZ active to input ignored		2		cycle
t_{PUS}	ZZ inactive to input sampled		2		cycle
t_{ZZI}	ZZ active to SLEEP current		2		cycle
t_{RZZI}	ZZ inactive to exit SLEEP current		0		ns

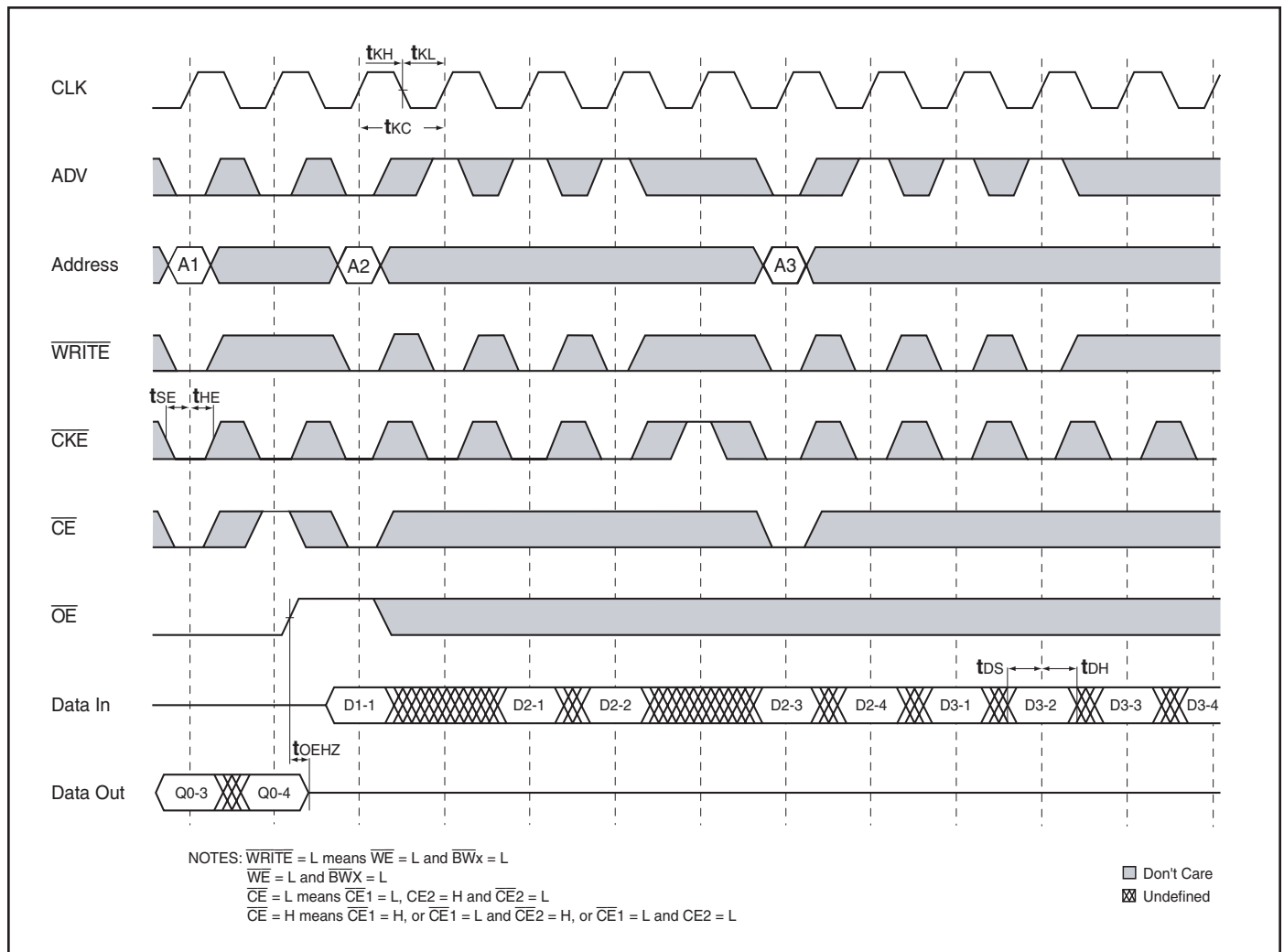
SLEEP MODE TIMING



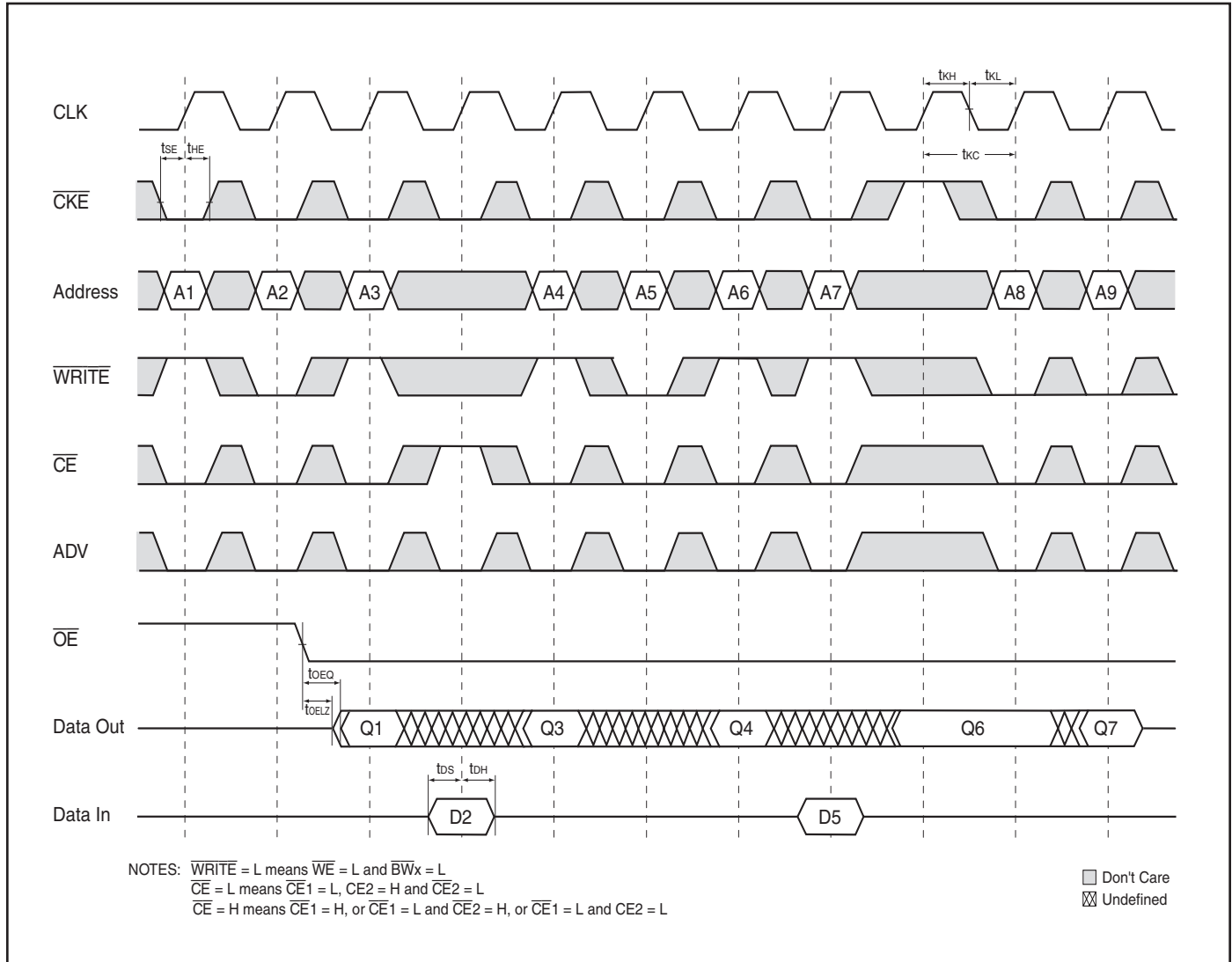
READ CYCLE TIMING



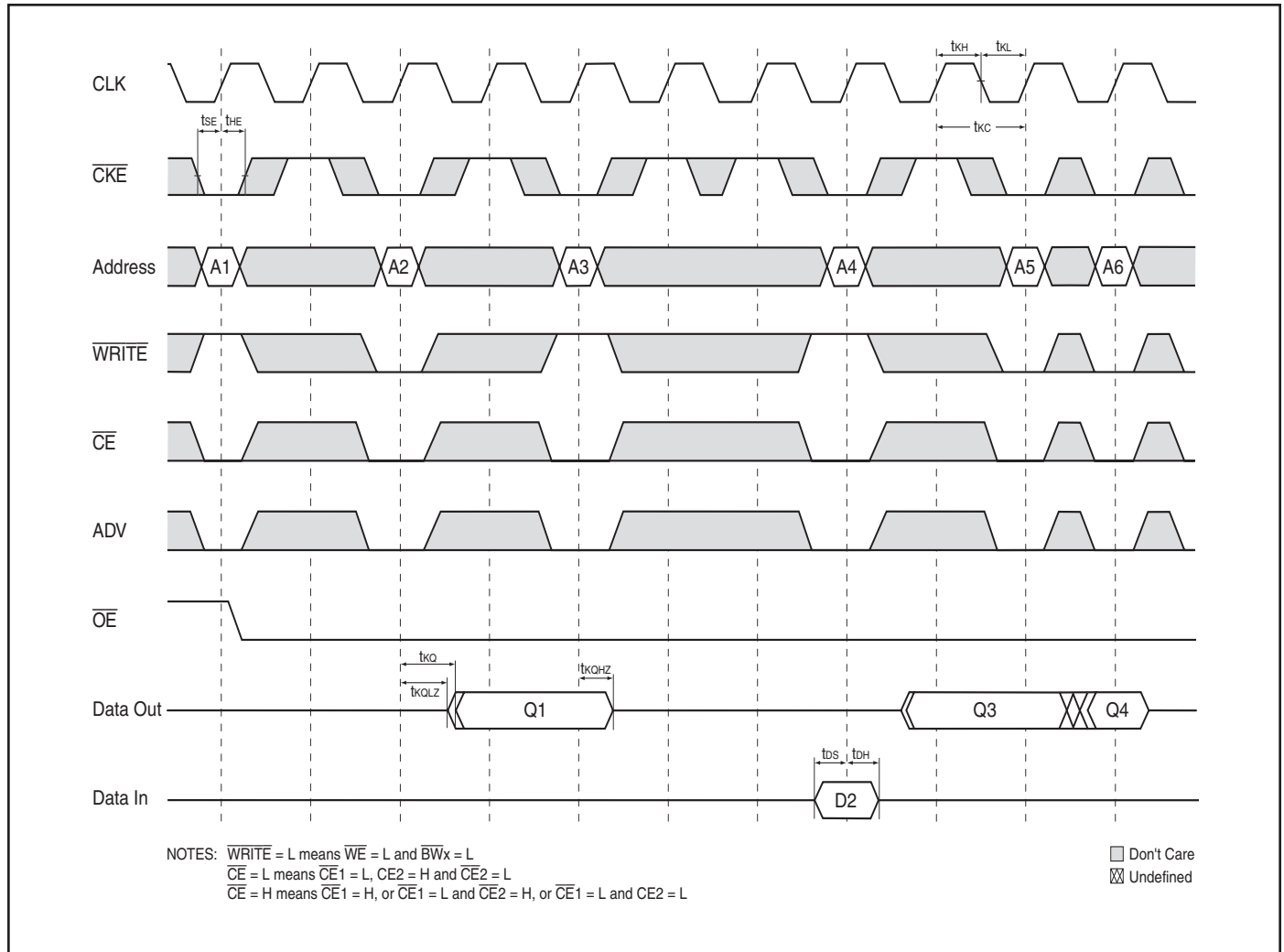
WRITE CYCLE TIMING



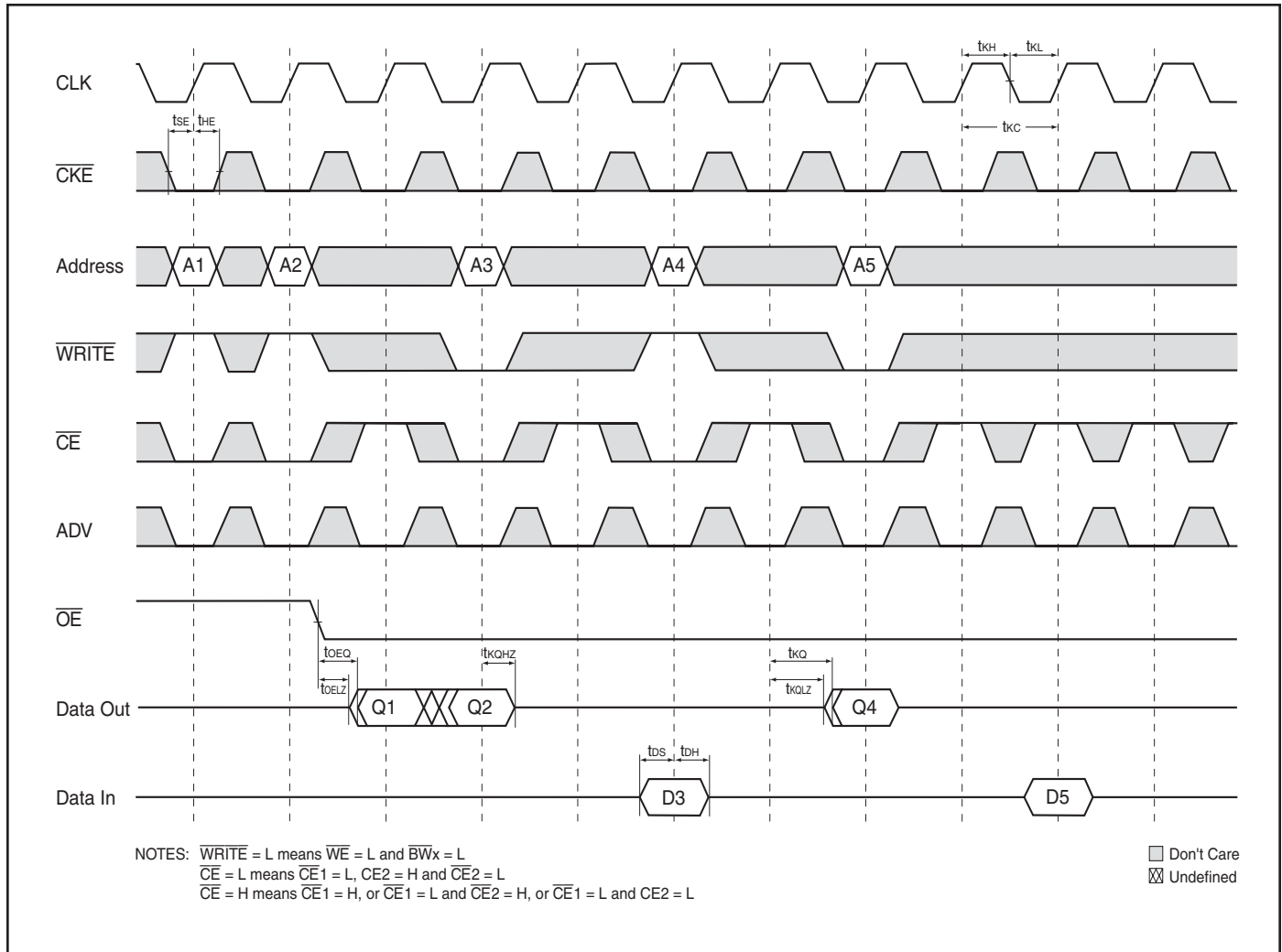
SINGLE READ/WRITE CYCLE TIMING



CKE OPERATION TIMING



CE OPERATION TIMING



IS61NLP6432A
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IS61NLP12818A/IS61NVP12818A



ORDERING INFORMATION (V_{DD} = 3.3V/V_{DDQ} = 2.5V/3.3V)

Commercial Range: 0°C to +70°C

Access Time	Order Part Number	Package
64Kx32		
250	IS61NLP6432A-250TQ	100 TQFP
200	IS61NLP6432A-200TQ	100 TQFP
64Kx36		
250	IS61NLP6436A-250TQ	100 TQFP
200	IS61NLP6436A-200TQ	100 TQFP
128Kx18		
250	IS61NLP12818A-250TQ	100 TQFP
200	IS61NLP12818A-200TQ	100 TQFP

Industrial Range: -40°C to +85°C

Access Time	Order Part Number	Package
64Kx32		
250	IS61NLP6432A-250TQI	100 TQFP
200	IS61NLP6432A-200TQI	100 TQFP
200	IS61NLP6432A-200TQLI	100 TQFP, Lead-free
64Kx36		
250	IS61NLP6436A-250TQI	100 TQFP
200	IS61NLP6436A-200TQI	100 TQFP
128Kx18		
250	IS61NLP12818A-250TQI	100 TQFP
200	IS61NLP12818A-200TQI	100 TQFP
200	IS61NLP12818A-200TQLI	100 TQFP, Lead-free